L Number	Hits	Search Text	DB	Time stamp
-	0	((("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and "silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/08 11:01
- ·	883	438/197.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:38
_	0	438/197.ccls. and "silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:45
_	106	"silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:37
-	21	"silicon germanium oxide" and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
-	17	"silicon germanium oxide" and epitaxial and deposition	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
_	15	"silicon germanium oxide" and epitaxial and deposition and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	14	"silicon germanium oxide" and epitaxial and deposition and gate and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	6	(("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:43
_	0	((("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and "silicon germanium"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	1	((("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and (silicon with germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	0	(("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and (silicon with germanium) and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:45
-	102	438/197.ccls. and "silicon germanium"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
_	99	438/197.ccls. and "silicon germanium" and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	48	438/197.ccls. and "silicon germanium" and oxide and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
	13	438/197.ccls. and "silicon germanium" and oxide and (epitaxial with deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	12	438/197.ccls. and "silicon germanium" and oxide and (epitaxial with deposition) and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14

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	3.5	"silicon germanium deposition"	USPAT;	2004/09/14
-	35	"Silicon germanium deposition"	US-PGPUB;	
		•		11:01
			EPO; JPO;	
			DERWENT	
-	20	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial	US-PGPUB;	11:01
			EPO; JPO;	
			DERWENT	
-	20	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4	US-PGPUB;	11:01
		1	EPO; JPO;	
		•	DERWENT	
l _	8	"silicon germanium deposition" and	USPAT;	2004/09/14
-		epitaxial and remov\$4 and gate	US-PGPUB;	11:02
		epitaxiai and removya and gate	EPO; JPO;	11.02
		•	DERWENT	
	' ہ	Haditana mammadam demonitrion Hond		2004/09/14
-	6	"silicon germanium deposition" and	USPAT;	
		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:02
1			EPO; JPO;	
			DERWENT	
-	5	"silicon germanium deposition" and	USPAT;	2004/09/14
	1	epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:02
		and transistor	EPO; JPO;	
			DERWENT	
-	l 0	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:03
		and transistor and protect\$4 and clean	EPO; JPO;	
		and clambible and proceess and erean	DERWENT	
	0	"silicon germanium deposition" and	USPAT;	2004/09/14
-	U	Silicon germanium deposition and otabéd	US-PGPUB;	11:03
		epitaxial and remov\$4 and gate and etch\$4		11.03
		and transistor and protect\$4 and ash\$4	EPO; JPO;	
			DERWENT	0004/00/14
-	2	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:32
		and transistor and protect\$4	EPO; JPO;	
			DERWENT	
_	0	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:33
	ļ	and transistor and protect\$4 and (wash or	EPO; JPO;	
		clean)	DERWENT	
<u> </u>	0	"silicon germanium oxide" near9 gate and	USPAT;	2004/09/14
_	1	epitaxial	US-PGPUB;	11:38
1		epicaxiai	EPO; JPO;	
			DERWENT	
		Waili and warmenium anidall maano gata	USPAT;	2004/09/14
-	2	"silicon germanium oxide" near9 gate		11:42
			US-PGPUB;	11.74
			EPO; JPO;	
			DERWENT	0004/00/14
-	658	"silicon germanium" near9 gate	USPAT;	2004/09/14
			US-PGPUB;	11:42
			EPO; JPO;	
			DERWENT	
-	231	"silicon germanium" near9 gate and	USPAT;	2004/09/14
		epitaxial	US-PGPUB;	11:42
		•	EPO; JPO;	
			DERWENT	
1_	195	"silicon germanium" near9 gate and	USPAT;	2004/09/14
[-	1,53	epitaxial and remov\$4	US-PGPUB;	11:46
		ebicavial and lemonda	EPO; JPO;	
			DERWENT	
		/		2004/09/14
-	9131	(oxide near9 gate) and epitaxial and	USPAT;	
İ		remov\$4	US-PGPUB;	11:46
			EPO; JPO;	
1			DERWENT	
1 -	1307	(oxide near9 gate) and epitaxial and	USPAT;	2004/09/14
		remov\$4 and "silicon germanium"	US-PGPUB;	11:46
		1	EPO; JPO;	
1			DERWENT	
_	1048	(oxide near9 gate) and epitaxial and	USPAT;	2004/09/14
1		remov\$4 and "silicon germanium" and	US-PGPUB;	11:47
		pattern\$4	EPO; JPO;	
		Paccetti,	DERWENT	1
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			·	10004/00/14
-	576		USPAT;	2004/09/14
		remov\$4 and "silicon germanium" and	US-PGPUB;	11:47
		pattern\$4 and oxidiz\$4	EPO; JPO;	
		l	DERWENT	
-	150		USPAT;	2004/09/14
		remov\$4 and "silicon germanium" and	US-PGPUB;	11:48 ·
•		pattern\$4 and oxidiz\$4 and (clean or	EPO; JPO;	
		wash)	DERWENT	
-	12		USPAT;	2004/09/14
		remov\$4 and "silicon germanium" and	US-PGPUB;	11:48
		pattern\$4 and oxidiz\$4 and (clean or	EPO; JPO;	
		wash) and recess	DERWENT	
-	12		USPAT;	2004/09/14
		remov\$4 and "silicon germanium" and	US-PGPUB;	11:48
		pattern\$4 and oxidiz\$4 and (clean or	EPO; JPO;	
		wash) and recess and etch\$4	DERWENT	1
-	12		USPAT;	2004/09/14
		remov\$4 and "silicon germanium" and	US-PGPUB;	11:49
· .		pattern\$4 and oxidiz\$4 and (clean or	EPO; JPO;	
		wash) and recess and etch\$4 and electrode	DERWENT	
-	10		USPAT;	2004/09/14
		remov\$4 and "silicon germanium" and	US-PGPUB;	11:49
		pattern\$4 and oxidiz\$4 and (clean or	EPO; JPO;	
		wash) and recess and etch\$4 and electrode	DERWENT	
		and dielectric		0004/00/14
-	10		USPAT;	2004/09/14
1	•	remov\$4 and "silicon germanium" and	US-PGPUB;	11:49
	ŀ	pattern\$4 and oxidiz\$4 and (clean or	EPO; JPO; DERWENT	
1	1	wash) and recess and etch\$4 and electrode	DERWENT	
	100	and dielectric and protect\$4	USPAT;	2004/11/03
_	109	"silicon germanium oxide"	US-PGPUB;	12:51
			EPO; JPO;	12.31
	1	·	DERWENT	
į	15	"silicon germanium oxide" and gate and	USPAT;	2004/11/03
-	15	epitaxial and above and remov\$4	US-PGPUB;	12:54
		ebicaviat and above and removal	EPO; JPO;	
			DERWENT	
_	2836	dielectric and electrode and protect\$4	USPAT;	2004/11/08
	2030	and etch\$4 and oxidiz\$4 and expos\$4 and	US-PGPUB;	11:51
		(semiconductor or wafer or substrate) and	EPO; JPO;	
		pattern\$4 and (clean\$4 or wash\$4)	DERWENT	[
l _	3	dielectric and electrode and protect\$4	USPAT;	2004/11/08
	l	and etch\$4 and oxidiz\$4 and expos\$4 and	US-PGPUB;	11:52
		(semiconductor or wafer or substrate) and	EPO; JPO;	
		pattern\$4 and (clean\$4 or wash\$4) and	DERWENT	
		("silicon germanium oxide" or SiGeO)		
	L	1		